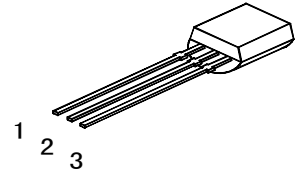


DESCRIPTION

The S9014 is an NPN epitaxial silicon planar transistor designed for use in the audio output stage and converter/inverter circuits.



S9014: 1. Emitter 2. Base 3. Collect

ABSOLUTE MAXIMUM RATINGS

Maximum Temperatures

Storage Temperature	-55~135 °C
Operating Temperature	135 °C
Lead Temperature (Soldering, <10s)	230 °C

Maximum Power Dissipation

Total Dissipation at 25 °C Ambient Temperature	0.4W
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Maximum Voltage

V_{CBO} Collector to Base Voltage	50V
V_{CEO} Collector to Emitter Voltage	45V
V_{EBO} Emitter to Base Voltage	5V
I_C Collector Current (continuous)	0.5A

ELECTRICAL CHARACTERISTICS (Ta=25 °C Unless otherwise noted)

SYMBOL	CHARACTERISTICS	MIN.	TYP.	MAX.	UNITS	TEST CONDITOMNS
H_{FE1}	DC current gain	60		1000		$I_C=1mA$ $V_{CE}=5V$
$V_{CE(SAT)}$	Collector Saturation Voltage			0.3	V	$I_C=100mA$ $I_B=10mA$
V_{BE}	Base-Emitter Voltage			0.85	V	$I_C=1mA$ $V_{CE}=5V$
BV_{CEO}	Collector to Emitter Breakdown Voltage	45			V	$I_C=1mA$ $I_B=0$
BV_{CBO}	Collector to Base Breakdown Voltage	50			V	$I_C=100 \mu A$ $I_E=0$
BV_{EBO}	Emitter to Base Breakdown Voltage	5			V	$I_E=100 \mu A$ $I_C=0$
I_{CBO}	Collector Cutoff Current			0.1	μA	$V_{CB}=50V$ $I_E=0$
f_T	Transition frequency	150				$I_C=10mA$ $V_{CE}=5V$ $f=30MHz$
C_{CB}	Collector to Base Capacitance			6	pF	$V_{CB}=10V$ $I_C=0$ $f=1MHz$

Note:

H_{FE1} classification: A: 60~150 B: 100~300 C: 200~600 D: 400~1000



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REV:0
25-May-05